Oral presentation | 13 Semiconductors | 13.8 Compound and power electron devices and process technology

[14a-B1-1~1]13.8 Compound and power electron devices and process technology

Seiji Nakamura(TMU)

Wed. Sep 14, 2016 11:45 AM - 12:15 PM B1 (Exhibition Hall)

△：Presentation by Applicant for JSAP Young Scientists Presentation Award

▲：English Presentation

▼：Both of Above

No Mark：None of Above

11:45 AM - 12:15 PM

[14a-B1-1][JSAP Paper Award Speech] Characterization of electronic states at insulator/(Al)GaN interfaces for improved insulated gate and surface passivation structures of GaN-based transistors

○Zenji Yatabe[1], Yujin Hori[2], Wancheng Ma[3], Joel T. Asubar[4], Masamichi Akazawa[3], Taketomo Sato[3], Tamotsu Hashizume[3] (1.Kumamoto Univ., 2.Furukawa Electric, 3.Hokkaido Univ., 4.Fukui Univ.)

Keywords:JSAP Paper Award